The Panopticon device - an integrated Paul-trap-hemispherical mirror system for quantum optics

G. Araneda, G. Cerchiari, P. C. Holz, K. Lakhmanskiy, and Y. Colombe
Institut für Experimentalphysik, Universität Innsbruck, Technikerstrasse 25, 6020 Innsbruck, Austria

D. B.. Higginbottom
Department of Physics, Simon Fraser University, Burnaby, British Columbia, V5A 1S6, Canada

P. Obšil
Department of Optics, Palacký University, 17. listopadu 12, 771 46 Olomouc, Czech Republic

R. Blatt
Institut für Experimentalphysik, Universität Innsbruck, Technikerstrasse 25, 6020 Innsbruck, Austria and
Institut für Quantenoptik und Quanteninformation, Österreichische Akademie
der Wissenschaften, Technikerstrasse 21a, 6020 Innsbruck, Austria
(Dated: June 11, 2020)

We present the design and construction of a new experimental apparatus in which a single Ba\textsuperscript{+} ion is trapped in the center of curvature of an optical-quality hemispherical mirror. We describe the layout, fabrication and integration of the full setup, consisting of a high-optical access monolithic “3D-printed” Paul trap, the hemispherical mirror, a diffraction-limited in-vacuum lens (NA=0.7) for collection of atomic fluorescence and a state-of-the art UHV vessel. This new apparatus enables the study of quantum electrodynamics effects such as strong inhibition and enhancement of spontaneous emission, and also increases the collection efficiency of the emitted light in a single optical mode up to 38%.

I. INTRODUCTION AND MOTIVATION

Atomic ions confined and laser-cooled in Paul traps provide an experimental platform to study quantum objects with a unique level of control. This is a consequence of the few-nanometers degree of localization, the long trapping time and the high fidelity manipulation of internal and external degrees of freedom\cite{1}. These features have been used extensively to build quantum information processors (see e.g., Ref.\cite{2}, and for the study of fundamental phenomena in quantum optics and atomic physics (see e.g., Ref.\cite{3}).

One of the most fundamental and intriguing phenomena in quantum optics is spontaneous emission and its modification\cite{4,7}. The spontaneous emission of atoms can be enhanced or inhibited in several ways. One way to modify the spontaneous emission rate is through dipole-dipole interactions between different atoms, namely sub- and superradiance-type effects\cite{8,11}. This has been extensively studied in neutral atom systems and used for diverse applications (see for example Refs.\cite{12-20}). In general it is difficult to observe large modifications of the spontaneous emission with trapped ions using this approach, since the Coulomb interaction restricts the minimum achievable inter-ion distance. Nevertheless, some degree of modification has been shown for the case of two ions. In Ref.\cite{21} enhancement of $\sim 1.5\%$ and inhibition of $\sim 1.2\%$ were observed by locating two ions 1470 nm away from each other.

Another way to enhance or reduce the rate of spontaneous emission of an atom is by modifying the electromagnetic vacuum mode structure interacting with the atom\cite{22,23}. The electromagnetic mode structure can be altered by placing the atom close to dielectric interfaces\cite{24}, between two mirrors\cite{25} or inside photonic structures producing a bandgap\cite{26}. In particular, large enhancement of the emission from a single atom has been achieved using high-finesse cavities\cite{27-30}. Recently, a 5-fold enhancement in the spontaneous emission rate has been demonstrated by placing a single atom in a fiber cavity\cite{31}. Furthermore, in the realm of solid state emitters, enhancement by a factor of more than 100 has been observed using microcavities\cite{32}. The opposite effect, i.e., strong inhibition of the spontaneous emission, remains elusive and only few experiments have demonstrated large modifications, see for example Ref.\cite{33} where the rate of spontaneous emission of a single Rydberg atom was reduced by a factor of 20, or Ref.\cite{34} where the emission rate of a solid state emitter was reduced by a factor of $\sim 10$. In ion trap systems, strong coupling between a single trapped ion and a fiber cavity has been recently observed\cite{35}. The main limitation in all the mentioned experiments is that by using standard approaches based on cavities it is not possible to restrict all the spatial modes of the spontaneous emission.

It is a common assumption in the field of cavity electrodynamics that to achieve total inhibition of the spontaneous emission it is necessary to place the atom in between mirrors that cover the full solid angle around it, restricting all the vacuum modes resonant with the atom, see for example Ref.\cite{6}. However, given the point symmetry of the atomic emission, it is still possible to access all the vacuum modes by covering only half of the solid angle. This can be achieved by placing the atoms in the center of a concave hemispherical mirror, as theoretically predicted in Ref.\cite{36}. Taking this approach, it appears to be possible to achieve both inhibition and enhancement of the spontaneous emission, depending on the distance.
Modification of the emission of an atom in the center of a hemispherical mirror. Depending on the radius and numerical aperture of a spherical mirror it is possible to observe inhibition or enhancement of the spontaneous emission rate of an atom located in its center of curvature. If the radius of the mirror is \( R = n\lambda/2 \), the center of curvature is a node of the vacuum mode density and inhibition is expected (blue curve). If the radius of the mirror is \( R = n\lambda/2 + \lambda/4 \), the center of curvature is an anti-node of the vacuum mode density and enhancement is expected (orange curve). Perfect inhibition and enhancement are achieved only in the case that half of the space is covered by the mirror (NA = 1). In this plot a mirror with perfect reflectivity is assumed. Reproduced from Ref. [36].

In this article we present the new “Panopticon”[37] apparatus for the integration of a high-quality hemispherical mirror (NA \( \approx 1 \)) and a Paul trap for the realization of the situation described above. In addition to the fundamental components of such a setup, i.e., the hemispherical mirror and a Paul trap, a high numerical aperture lens (NA = 0.7) is used to collimate the emission and direct it to a detector, as shown in Fig. 2. The design and construction of such an apparatus presents multiple technical challenges which are discussed in this paper, including:

- In section II A we discuss the construction and characterization of a hemispherical mirror with constant radius of curvature. The effects discussed above vanish rapidly if the radius of curvature is not constant. We aimed to fabricate a hemispherical mirror with an RMS radius of curvature error not larger than \( \lambda/10 \) over all the surface. The radius of curvature must be tunable in order to access both inhibition and enhancement of the spontaneous emission. This can be achieved through thermal expansion of the substrate.
- In section II B we discuss the design and characterization of the high-NA lens used for collection. The lens design aims at diffraction-limited performance, enabling interference and imaging experiments such as the ones presented in Refs. [38, 40].
- In section II C we discuss the trap design. The used Paul trap must provide full optical clearance between the trapped ion and the hemispherical mirror. Additionally, it must provide optical access for the collection of the emitted light through the high-NA lens and for laser access. Ideally, the trap should also provide the possibility of trapping several ions simultaneously in a stable fashion to provide enough flexibility for quantum optics experiments such as the one presented in Ref. [39].
- In section II D we discuss the integration of the mirror, trap and lens. The position of the optical elements should be adjustable in-situ, with nanometer precision.
- In section II E we present the design of the vacuum vessel. All the above mentioned elements have to be placed in an ultra high vacuum environment, which contains an atomic source and all the necessary electrical and optical access.

Besides the fundamental interest on measuring effects predicted by quantum electrodynamics[36], being able to control the spontaneous emission of a dipole transition has several applications. For example, reducing the decay rate two orders of magnitude on a dipole transition would increase the efficiency of the overall optical system, with wavefront errors below \( \lambda/10 \) for all the components, the collected light can be captured in a single mode and coupled efficiently to a single mode fiber[43].
The high collection efficiency and the cleanness of the optical mode is expected to improve the signal to noise ratio of any optical measurement of atomic properties. Additionally, the improved collection and absorption rates enabled by this setup could be used to implement a quantum network without cavities [44, 45].

We note that some of the features exhibited by a setup employing a hemispherical mirror, such as high collection efficiency and improved single photon absorption, can be achieved using an atom in the focus of a parabolic mirror [46, 47]. Indeed, in Ref. [47] collection efficiencies as high as 54.8% have been reported using a parabolic mirror. However, in this approach, the enhancement and inhibition of the spontaneous emission due to QED effects vanish for macroscopic parabolic mirrors [46]. Other approaches consist of using a combination of a high-NA lens collecting the light emitted by an atom and a mirror retroreflecting the collected light. Although changes in the decay rates have been observed using this method [48], the maximum modifications are limited by the achievable numerical apertures of the collection lens in trapped ions systems. Furthermore, previous attempts to position an ion in the center of a spherical mirror have proved stable trapping and improved light collection [49], but they have not achieved the mirror surface quality, radius tunability and numerical aperture required to show inhibition or suppression of the spontaneous emission.

II. THE PANOPTICON SETUP

The main feature of the Panopticon setup is the ability to confine a single trapped atomic ion in the center of a hemispherical mirror. The ion trap needs to provide full optical access between the trapped ion and the mirror. Additionally, in order to capture a large portion of the emitted field, a high-NA aspheric lens (NA = 0.7) is positioned opposite to the mirror, such that its focal point lies at the position of the ion. Therefore, the trap needs also to provide optical access for the solid angle captured by the asphere. Fig. 2 shows a schematic with the main components of the Panopticon setup. In the following sections we describe the design, construction and characterization of each of these main components, and how they are assembled together.

A. The hemispherical mirror

The main component of the Panopticon setup is the concave hemispherical mirror. Results about the fabrication and characterization of this mirror have been previously published in Ref. [50]. To observe a large modification of the spontaneous emission of an atom located in its center, a constant radius of curvature is required over the full numerical aperture. To our knowledge, the best macroscopic round objects ever fabricated are spheres with a surface deviation of only 17 nm peak-to-valley [51]. This surface quality is achieved by randomly rotating the sphere between two polishing tools, for periods of several days. Unfortunately, this technique cannot be applied to concave spherical surfaces, and in general, until now, there was no technique able to produce a surface precision similar to that of a convex sphere.

In collaboration with the Australian National University (ANU) we have been able to produce hemispherical mirrors with RMS form errors consistently below 25 nm, a maximum peak-to-valley error of 88 nm, and a radius of curvature of ≈ 12.5 mm. The mirrors were fabricated by diamond turning a cylindrical aluminium 6061 substrate with a CNC (computer numerical controlled) nano-lathe [52]. To achieve low surface deformation, an in-situ white-light interferometer was implemented on the lathe, permitting the calibration of the tool with...
sub-nanometer precision prior to the machining. A detailed description of the fabrication and characterization of the mirrors can be found in Refs. 50 and 53.

Fig. 3 shows one of the fabricated mirrors, with a surface RMS error of 18.1 nm (λ/27 for λ = 493 nm) and a peak-to-valley error of 116.5 nm estimated using stitch interferometry (see Ref. 50 for details). There are two drilled holes (3 mm diameter) which provide laser access to the center of curvature, where the ion will be located (see Section II D). One of the holes is located along the optical axis of the mirror and the other at 62° with respect to the optical axis. The NA of this mirror is 0.996 (half aperture 85°), which is not a limitation of the fabrication process but is planned to provide optical clearance (1.1 mm) to the trapped ion for laser access orthogonal to the mirror’s optical axis. The reflectivity of the mirror is given by the reflectivity of the substrate (0.92 for aluminium 6061 at 493 nm), and it could be improved by applying a highly reflective thin film coating to the mirror. Nevertheless, the concave shape of the mirror makes it difficult to realize this in a uniform fashion, and it would be detrimental for the overall surface quality using standard techniques [54]. Detrimental effects are expected also from standard polishing techniques.

Fig. 4 shows the expected modification of the spontaneous emission considering the measured surface form, reflectivity and the effect of the drilled holes. Considering form and reflectivity, the maximum expected enhancement and inhibition of the spontaneous emission rate in the 493 nm transition in $^{138}\text{Ba}^+$ correspond to 88% of their ideal values. The main deviation from the ideal case comes from the limited reflectivity of the material.

The mirrors have been shown to be resilient to a cycle of vacuum bake-out at typical conditions (maximum temperature of 200 °C).

1. Temperature stabilization and tuning of the radius of curvature

To tune the radius of curvature of the mirror, we rely on the uniform thermal expansion of the substrate. The coefficient of thermal expansion of aluminium 6061 at room temperature is $23.5 \times 10^{-6} \text{ K}^{-1}$ [55]. To achieve a difference in the radius of curvature of $\lambda/4 \approx 123.3 \text{ nm}$ (with $\lambda = 493 \text{ nm}$) it is necessary to change the temperature by 0.42 K. Heating the mirror under a single-shot white-light ZYGO interferometer has shown tunability over the desired range in a uniform fashion, and no indication of surface distortion due to thermal expansion. Nevertheless, small variations in environmental temperature could lead to drifts in the radius of curvature, therefore, active stabilization of the temperature of the mirror is necessary.

To control and stabilize the temperature of the mirror we designed a resistively heated holder, shown in Fig. 5. The holder is heated by applying current to a self-wrapped heating wire [56]. The temperature of the holder is measured in the back of the holder using two temperature sensors [57], which are glued to the holder [58]. The mirror is not directly contacted to the holder but it lies on ceramic rods [59] and glass spheres [60] (see Fig. 5), providing a distance of 1.1 mm between the exterior surface of the mirror and the inside of the holder. Therefore, the heat transfer between the holder and the mirror is mostly radiative. This provides a constant temperature on the mirror volume, although with a slow temperature tuning rate. The temperature is stabilized with a feedback loop using a high precision PID [61]. In-vacuum tests have shown a mirror temperature stability below 1 mK over 10 hours, with set points varied between 293 and 303 K. The heating time constant of the mirror has been measured to be 5.39 hours, while the cooling time constant (cooling is achieved passively) is 3.89 hours. These times could be reduced by increasing the thermal contact between the mirror and the holder, which would, however, compromise the achieved stability. The PID can be operated in sample and hold or constant current regime. This is useful for sensitive atomic measurements where a constant magnetic field could be required. The achieved temperature stability corresponds to local radius of curvature fluctuations below the actual surface error of the fabricated mirror.

B. The aspheric lens

To capture and collimate the light emitted by the ion, an aspheric lens is located opposite to the hemispherical mirror, as shown in Fig. 2. The main advantages of using an aspheric lens instead of a multi-lens objective are the simple compact design and the reduced spherical and other optical aberrations. The low aberrations play a crucial role for future experiments related with spatial properties of emitted and absorbed photons, as well as interference experiments with photons emitted by atoms in different traps coupled with optical fibers and optical detection of quantum features of the atomic motion.

The asphere, designed and fabricated by Asphericon GmbH, has an NA = 0.7, a working distance of 9.60 mm
FIG. 5. **Mirror holder and heater.** Components of the mirror’s aluminium holder and heater used to achieve a mirror temperature stability below 1 mK. The right-most photograph shows the setup used during the temperature stability tests performed in vacuum, with a thermistor attached directly to one of the mirrors.

and an effective focal length of 16.05 mm. The design was optimized using Zemax OpticStudio to achieve a diffraction-limited single lens with ultra-low wavefront aberrations at 493 nm. The dimensions of the designed asphere are shown in Fig. 6. The surface facing the ion has a designed constant radius of curvature \( R_B = 202.4 \text{ mm} \), whereas the opposite face is a rotation symmetric asphere defined by the equation

\[
z(r) = \frac{r^2}{R_F \left(1 + \sqrt{1 - (1 + k) \frac{r^2}{R_F^2}}\right)} + \sum_{i=2}^{\infty} A_{2i} r^{2i}.
\]

The values of the parameters \( R_F \), \( k \) and \( A_{2i} \) are listed in Table I.

![Aspheric lens dimensions](image)

**FIG. 6. Aspheric lens dimensions.** The surface facing the ion is spherical with a radius of curvature \( R_B \), whereas the aspheric face is defined by the Eq. 1. The ion is positioned 9.6 mm away from the front surface. The aspheric surface design parameters are listed in Table I.

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Value</th>
</tr>
</thead>
<tbody>
<tr>
<td>( R_F )</td>
<td>14.56 mm</td>
</tr>
<tr>
<td>( k )</td>
<td>-0.776</td>
</tr>
<tr>
<td>( A_4 )</td>
<td>(-3.2022806 \times 10^{-6}) mm(^{-3})</td>
</tr>
<tr>
<td>( A_6 )</td>
<td>(-2.9002661 \times 10^{-8}) mm(^{-5})</td>
</tr>
<tr>
<td>( A_8 )</td>
<td>(-9.6249910 \times 10^{-11}) mm(^{-7})</td>
</tr>
<tr>
<td>( A_{10} )</td>
<td>(-1.0236456 \times 10^{-13}) mm(^{-9})</td>
</tr>
<tr>
<td>( A_{12} )</td>
<td>(4.5511459 \times 10^{-16}) mm(^{-11})</td>
</tr>
<tr>
<td>( A_{14} )</td>
<td>(3.3201252 \times 10^{-18}) mm(^{-13})</td>
</tr>
<tr>
<td>( A_{16} )</td>
<td>(-8.7645298 \times 10^{-21}) mm(^{-15})</td>
</tr>
</tbody>
</table>

Three pieces of the designed asphere were fabricated using a S-TIH53 glass substrate, with refractive index \( n_g \approx 1.85 \) and Abbe number \( v_g = 23.59 \) (at 546 nm). The manufacturing process includes CNC grinding and polishing as a first step. Thereafter, ion beam figuring is used in order to reduce surface irregularities. In this process, ion beams are directed at specific regions of the surface where surface errors have been detected. Finally, an anti-reflective coating for 493 nm is applied using plasma-assisted physical vapour deposition. All these steps were performed using Asphericon GmbH technology. Fig. 7a shows a photograph of one of the aspheres and Fig. 7b shows the achieved wavefront quality. RMS wavefront distortions below 37 nm (\( \lambda /14 \)) and peak-to-valley distortions below 700 nm over the full numerical aperture were systematically achieved. From Fig. 7b, it is clear that the most dramatic surface deformations occur close to the lens edge. In fact, by reducing the aperture of the lens to \( NA = 0.65 \), the RMS wavefront error is reduced to \( \lambda /24 \). The reflections in the coated surfaces were measured to be smaller than 0.4% for incidence angles of up to 40°, and the transmittivity measured with a laser beam perpendicular to the surface at the...
center of the lens was 95%, in agreement with the expected values. Both measurements were done with a laser beam with a 493 nm wavelength.

The lens is mounted in an aluminium holder, which allows for laser access to the focal point of the lens from several directions (see Section II D), and with negligible reduction of the numerical aperture.

C. The ion trap

The main challenge in the design of an ion trap compatible with the Panopticon setup is that the trap should provide full optical access between the trapped ion and the hemispherical mirror, but also between the ion and the aperture defined by the aspheric lens. This could be achieved using, for example, a needle trap [66]. However, this approach allows the trapping of only one ion without excess of micromotion. It is desirable to be able to trap several ions stably, since the setup could then be used for a broader range of quantum optics experiments. There are some designs which partially comply with the optical access and stable trapping of several ions criteria, including, for example, the miniaturized segmented “High Optical Access Trap 2.0” developed by the Sandia National Laboratories [67]. However, this trap only possesses a clear aperture equivalent to $\text{NA} = 0.25$. The approach that we take here is the fabrication of a monolithic slotted pseudo-planar macroscopic trap. A simplified scheme of the trap geometry, with only the minimal electrode configuration needed to trap an ion, is shown in Fig. 8. Later in this article, we discuss the actual fabricated trap with additional features.

The fabrication is done with subtractive 3D laser micro-machining technology. The basic idea is to 3D laser machine a monolithic dielectric substrate with the required shape, including “trenches” to separate different regions. In the following, we will refer to this technique as “3D printing”. The surfaces are then coated with gold, creating isolated electrodes in each region surrounded by trenches. Fig. 9 depicts how 3D-
First, a dielectric substrate is “3D-printed” to create the trenches needed to separate electrodes. Then, the surfaces are coated with a conductor (gold). The geometry of the printed trenches provides electric insulation between different regions, defining different electrodes.

The required precision of the dielectric substrate fabrication can be achieved by “laser carving” techniques provided by companies such as FEMTOprint SA in Switzerland or Translume Inc in USA. The 3D-printing technology used by these companies employs strongly-focused high-energy laser pulses to locally change the refractive index of the substrate. Then a photo-chemical process is used to remove the material with altered refraction index. Using this technique on, e.g., fused silica, the carved features can reach an average roughness below 100 nm, whereas the untouched surfaces can reach an average roughness below 5 nm. Additional polishing can reduce the roughness below 50 nm, though with detrimental effects in surrounding areas. A more detailed description of this technology applied to the fabrication of ion traps can be found in Ref. [68].

The conductive coating is carried out in our clean room by means of electron beam evaporation of a thin layer of titanium (∼2 nm), used as adhesion promoter, followed by a thick layer of gold (∼200 nm). Gold evaporation is applied from three different angles at each side. Gold electroplating is used afterwards to increase the thickness of the electrodes to ∼5 μm.

1. Simulations of the trapping potential

The trap geometry presented in Fig. 8 is the result of a systematic optimization. The different dimensions and positions were varied to maximize the trapping frequencies for a $^{138}$Ba$^+$ ion, as well as the trap depth, reduce the trap capacitance, the residual axial RF field and to maximize the ion-electrode distance, which is constrained by the required optical clearance and laser access to the ion. For these purposes, the electric potentials produced by the trap electrodes are simulated via finite element analysis using the software COMSOL Multiphysics 4.4. In these simulations the grounded hemispherical mirror is included.

Fig. 10 shows the total trapping potential. The RF pseudopotential minimum is located 157 μm away from the front plane, making the distance of a trapped ion and the closest electrode equal to 453 μm. For comparison, in our current “Innsbruck-style” blade trap[69] this distance is 707 μm. Small distances between the ion and electrodes increase the ion heating rate due to surface noise and other effects [70]. Keeping this distance relatively large is important to minimize these effects.

Fig. 10c shows the trapping potentials along each coordinate axis. The potentials along x and z are symmetric about the trap center, while along the y axis it is asymmetric, as typically observed in surface traps [66]. Depending on the volt-
ages applied to the different electrodes, the trapping frequencies can be varied. Table II shows the trapping frequencies and trap depths obtained from the simulations for a $^{138}$Ba$^+$ ion. The trap depths are in the eV regime, comparable with 3D rod and depths, obtained by finite elements simulations for $^{138}$Ba$^+$. Three different configurations are shown. DC1 and DC2 correspond to the “endcap” electrodes shown in Fig. III while DC3, DC4, DC5 and DC6 are the electrodes in the back plane. In these three configurations the electrodes G1, G2, G3, G4 and the mirror are grounded.

Table II. Trap driving parameters and resulting trap frequencies and depths, obtained by finite elements simulations for $^{138}$Ba$^+$. III

<table>
<thead>
<tr>
<th>RF freq. $\Omega_{RF}/2\pi$ (MHz)</th>
<th>16.0</th>
<th>16.0</th>
<th>16.0</th>
</tr>
</thead>
<tbody>
<tr>
<td>RF amplitude $U_{RF}$ (V)</td>
<td>1000</td>
<td>1500</td>
<td>2000</td>
</tr>
<tr>
<td>DC1,2 (V)</td>
<td>200</td>
<td>300</td>
<td>400</td>
</tr>
<tr>
<td>DC3,4,5,6 (V)</td>
<td>82</td>
<td>123</td>
<td>164</td>
</tr>
<tr>
<td>$\omega_x/2\pi$ (MHz)</td>
<td>1.33</td>
<td>2.16</td>
<td>2.96</td>
</tr>
<tr>
<td>$\omega_y/2\pi$ (MHz)</td>
<td>1.57</td>
<td>2.34</td>
<td>3.07</td>
</tr>
<tr>
<td>$\omega_z/2\pi$ (MHz)</td>
<td>0.51</td>
<td>0.62</td>
<td>0.72</td>
</tr>
<tr>
<td>Trap depth (eV)</td>
<td>2.4</td>
<td>4.9</td>
<td>8.2</td>
</tr>
</tbody>
</table>

Simulations show that independent control of the voltages applied to the electrodes DC3, DC4, DC5 and DC6 is sufficient for compensation of micromotion in all directions. Further simulations with different trench geometries and dimensions were carried out. The most relevant trench parameter, i.e., the electrode-electrode separation provided by the trench, was varied between 50 $\mu$m and 150 $\mu$m. Variations in this range have a negligible effect on the trapping potential, so that the final dimensions were selected based on breakdown test results described in the following section.

2. The fabricated trap

While the fabricated trap has the same core geometry as the one presented in Fig. III, it includes additional features. Fig. III shows schematics and renders of the actual design. The ground electrodes in the front G1 and G2 have been divided into smaller electrodes GR1, GR2, GR3 and GR4 (see Fig. III) in order to add more flexibility for the compensation of micromotion. These electrodes together with all the other electrodes in the front plane (EC1, EC2, RF and GRB) are extended to reach the back plane. There, together with the back plane electrodes CU1, CU2, CU3, CD1, CD2 and CD3, they are prolonged into conductive traces to reach an area not covered by the mirror nor the lens (Fig. III). This flat and elongated design provides enough space around the trap to wire-bonded and connect the trap to the voltage supplies through a printed circuit board (PCB, see Section III). In this way, no wire will reduce the optical clearance near the trapping region. The extended area is also used to clamp the trap to the PCB using the drilled holes.

Additionally, grooves in the front face are carved in the substrate (during the 3D-printing process). These grooves improve the clearance of the laser beams that propagate close to the surface, reducing the light scattered by the trap. This is of particular importance when addressing single ions using a strongly focused 1.7 $\mu$m laser. The conical vertical grooves shown in Fig. III match the divergence of such a laser with additional 100 $\mu$m of optical clearance. The horizontal cylindrical grooves give enough optical clearance for lightly focused axial cooling and optical pumping beams. Fig. III shows transversal cuts at the trap center, showing the position of the ion and the optical clearance provided by the design. The dimension of the trenches separating adjacent electrodes, shown in Fig. III, were chosen after performing DC and RF breakdown tests in a simplified trap. The separation between electrodes was varied between 50 and 150 $\mu$m. These tests did not show any sign of electric breakdown between electrodes at DC voltages as high as 700 V and RF voltages as high as 1200 V at 20 MHz. The distance was finally chosen to be 100 $\mu$m. The bottom of the trenches is connected to the common ground GR B. A complete 3D drawing of the designed trap can be found in the supplementary material. Fig. III shows a photograph of one of the traps fabricated by FEMTOprint S.A. before metalization.

We have performed simulations of the generated trapping potential for the fabricated trap design, including all the aforementioned features. The differences with the results of the simulations of the simplified version presented in section III C are negligible.

3. Trap holder, in-vacuum low-pass filter and voltage driving

The ion trap is mounted on an aluminum holder plate (2 mm thickness) using four screws, as shown in Fig. III. This holder plate also acts as a heat sink for the trap and is contacted to the body of the vacuum chamber. This plate also holds a filter PCB. The trap is wire-bonded to the PCB using gold wires. The PCB, made of alumina [72] with a thickness of 1 mm, has 16 silk-printed gold traces, wire-bond pads, paths and soldering pads [73] for DC and RF routing. There are 8 vias to guide some of the paths to the opposite side of the PCB. All the DC paths are capacitively coupled to a common ground using 1 nF high voltage surface mounted capacitors [74], suppressing RF pick up. Additionally, 1 k$\Omega$ ex-vacuum resistors are used in order to filter high frequency noise induced in the DC electrodes (cutoff frequency 1 kHz). Fig. III and c show a schematic view of the PCB. At the edge opposite to the trap, the PCB has 16 gold pins [75] soldered [76], allowing easy connection and disconnection of each line to copper wires which are attached to the electrical feedthroughs on the base vacuum flange (see Fig. III). None of the PCB traces or the wires are exposed to the atomic flux from the atom source (see section III A).

The DC voltages are generated outside the vacuum chamber using a high-precision high-voltage source [77]. The RF voltage is generated using a high precision signal generator [78].
D. System integration

The optical setup, consisting of the hemispherical mirror, the aspheric lens and the ion trap, has to be set in place in a robust and stable manner, while still providing enough degrees of freedom for correct alignment. The holders and positions have to be compatible with the ultra-high vacuum environment needed to trap single atomic ions in a stable way. To do so, we designed the mounting system shown in Fig. 14. In this setup, all the elements are carefully designed in order to provide the required laser access and optical clearance. The

FIG. 11. Full design of the ion trap. a. Front side of the final trap design. Cylindrical and conical grooves are carved in the substrate in order to minimize the scatter of laser beams propagating close to the surface. All the electrodes in the front are extended to the back plane through the edges. b. In the back plane all the electrodes are extended into rails, which are used for wire-bonding to connect to the voltage supplies. c. Transversal cut at the trap center showing the optical clearance provided by the trap. d. Dimensions of the trenches separating the electrodes. followed by a 28 dB amplifier and a helical resonator.
FIG. 12. Fabricated ion trap. Fabricated ion trap before metallization.

FIG. 13. Trap holder and filter PCB. Both the trap and the PCB filter are mounted in a aluminum holder. The trap is wire-bonded to the PCB which contains conducting paths, capacitors and pins for connecting to the DC and RF sources.

FIG. 14. Panopticon optical setup. The mirror and lens are mounted on independent xyz-nanopositioners, whereas the position of the ion trap is fixed. The blue lines show the four laser axes.

The position of the mirror and the lens can be independently set using xyz-nanopositioners shown in the figure. The positioners have a step size of 1 nm in each direction, a position read resolution of 1 nm and a maximum displacement of 12 mm.

III. THE VACUUM VESSEL

The Panopticon optical setup is placed in an ultra-high vacuum environment. To achieve this we have used the vacuum vessel shown in Fig. 15. The main component of the vacuum vessel is an 8"-CF spherical octagon vacuum chamber.

A customized 6-way CF cross is attached to the main chamber, providing enough flanges to connect a vacuum valve, a vacuum gauge, the electric feedthroughs for the wiring of the nanopositioners, a non-evaporable getter (NEG) pump and a viewport. The main pumping UHV
is done with a combined ion and NEG pump\cite{86} attached to the main chamber. During the NEG activation, the pump can reach temperatures close to 450°C. This temperature is not compatible with the maximum temperature to which the nanopositioners can be exposed (150°C). In order to avoid damaging the nanopositioners, the pump is retracted from the main chamber using a spacer, and a two-layer aluminium heat shield is placed between the pump and the positioners (see Fig.\textcolor{black}{15}). According to simulations performed by the pump manufacturer this is sufficient to prevent damage of the nanopositioners.

The vacuum vessel has all the necessary viewports to provide access to the center of the trap using the planned axes (see Fig.\textcolor{black}{14}), including a CF-160 viewport on the top of the chamber. All the viewports\cite{87} are anti-reflection coated for all the wavelengths needed to load, cool and control $^{138}$Ba$^+$ ions, i.e., 413, 493, 614, 650 and 1762 nm. For all the relevant wavelengths the reflectivity is below 1%. The viewport used for transmitting the light emitted by the ion and collimated by the aspheric lens has an optical quality surface, with wavefront aberrations below $\lambda/10$ over all the surface (with $\lambda = 493$ nm)\cite{88}. An additional Germanium viewport\cite{89} is located in the main chamber, with the purpose of monitoring the temperature of the atom oven using a thermal camera (see

\textbf{FIG. 15. Vacuum vessel main components.} See details in the main text.
The electrical connections needed to drive the ion trap, to heat an atom dispenser and to measure and control the temperature of the mirror are routed through feedthroughs in the customized CF-160 bottom flange. This customized flange also has a CF-16 viewport intended for 1.7 \( \mu \)m laser addressing of individual trapped ions.

### A. Atom source

To provide a source of atoms inside the vacuum chamber, we have designed a loading stage that simultaneously contains a resistively heated Ba dispenser and a laser ablation target. The resistively heated dispenser is a reliable way to produce a flux of neutral atoms in the center of the trap, which are then ionized using a 413 nm laser through a two-step excitation process. This process is, however, slow, and produces an excess of heat inside the vacuum chamber that can have detrimental effects on the operation of ion traps, such as undesired thermal expansion of the mirror and thermal expansion of the electrodes.

Laser ablation from a target is an alternative method, which has been proved to be more efficient and less detrimental for operating ion traps (see for example Ref. [90]). In this case, short and strong laser pulses are applied on a Ba target to produce neutral and ionized atoms, which eventually reach the center of the trap. It has been experimentally shown that instead of using a pure Ba target, targets containing BaTiO\(_3\) or BaO produce higher Ba\(^{+}\) yields [91], making loading more efficient and without the requirement of additional photionization lasers. At the same time, using BaTiO\(_3\) instead of pure Ba prevents fast oxidation of the sample during the vacuum preparation.

Fig. 16 shows the designed loading stage, where both a resistive oven (dispenser) [92] and a BaTiO\(_3\) ablation target [93] are located. The holder is made of macor\textsuperscript{\textregistered} ceramic, which exhibits a low thermal and electric conductance. Both the target and the oven are enclosed in a copper shield, which simultaneously provides thermal insulation and prevents the ablated Barium from spreading into the rest of the chamber and into the trap. Two circular apertures in the front are used to collimate the atomic flux and direct it to the center of the ion trap. As the ablation process spreads atoms in every direction, a mirror and a hole in the shield are used for the ablation laser pulses. This configuration prevents a high atomic flux from exiting the shield and directly coating the viewport used for the ablation laser (CF-160). These features are important to avoid coating the viewports in the long term and to avoid the shortening of trap electrodes due to the atomic flux. Additionally, there is a small square aperture in the side, which allows for in-situ monitoring of the oven temperature with a thermal camera through an infra-red transmissive Germanium viewport. This can be used to study the heating dynamics of the oven in ultra-high vacuum and to optimize the loading process avoiding excess heating [94].

A broad range of pulsed laser sources can produce the pulses needed for ablation. An example of such a source is a pulsed diode pumped solid state laser (DPSS), with a wavelength of 515 nm and energy per pulse of 170 \( \mu \)J [95]. This wavelength is compatible with our coated viewports.

### B. Vacuum preparation and ex-vacuum elements

The cleaning of all the vacuum elements is done following the procedure described in Ref. [96]. After sealing the vacuum chamber and vacuum baking we have achieved a pressure below 10\(^{-10}\) mbar.

Three pairs of magnetic field coils are attached to the outside of the main chamber flanges in order to provide a homogeneous magnetic field at the center of the trap. This coils can be easy replaced by rings of permanent magnets in order
FIG. 17. Step mirror concept. A mirror with radius of curvature $R_1 = n\lambda/2$ around the center and $R_2 = n\lambda/2 + \lambda/4$ further out would permit to enhance the emission of photons in the collected solid angle while inhibiting the emission outside.

to achieve a better suppression of RF magnetic field noise. Four legs have been attached to the exterior of the vacuum chamber in order to support it on an optical table.

IV. SUMMARY AND OUTLOOK

In this article we have presented the design and construction of a new setup which will allow us to perform studies of quantum electrodynamics effects. Furthermore, the presented setup features an unprecedented single-mode collection efficiency. We have presented the design and construction of the main optical components of such a setup, namely a hemispherical mirror and an aspheric lens, and shown how the strict requirements on their fabrication can be fulfilled. We have shown that these optical elements present wavefront distortion below $\lambda/10$. This would allow the efficient coupling of the collected light into single mode fibers.

In particular, an unprecedented precision of the fabrication of macroscopic concave hemispherical mirrors has been achieved, which will give us access to enhancement and inhibition of the spontaneous emission of a single atom of more than 96% of its free-space value. The technique used for their fabrication could be extended to the precise fabrication of other exotic quantum electrodynamics situations. One such example, proposed by Yves Colombe, would be the fabrication of a mirror with a $\lambda/4$ radius step, such as the one shown in Fig. 17. Such a mirror will allow us to enhance the spontaneous emission in the modes collected by a lens, while inhibiting the rest. In such a way, collection efficiencies close to 100% could be achieved using perfect a perfectly shaped mirror. For a mirror with a $\lambda/4$ step and fabrication accuracy as the one shown in section II A together with the lens presented in section II B an unprecedented 75% collection efficiency is expected.

We have also presented the design of a monolithic high optical access ion trap. Such a trap is compatible with the optical access required for the observation of the quantum electrodynamics effects. The trapping parameters are similar to those in state of the art macroscopic traps, such as our “Innsbruck-style” trap.

The physical phenomena that we aim to study with this setup, such as strong inhibition and enhancement of the spontaneous emission, are not restricted to atomic ions, but could be observed from any quantum emitter. Therefore, the optical setup presented here could be used with other systems with promising prospects in quantum networking and communications, such as quantum dots or diamond spin qubits.

ACKNOWLEDGMENTS

We thank Christoph Wegscheider and the rest of our mechanical workshop team for their advice and help with the fabrication of the mechanical components. We gratefully acknowledge the contribution of W. Shihua and colleagues at the National Metrology Centre, A*STAR in Singapore. Without their expertise and the use of their high-NA optical interferometer and contact-probe measurements the first stages of this work would not have been possible. We also thank the FEMTOprint, Elceram and Asphericon team for their advice and smooth collaboration. We thank Lukas Slodicka, Martin Van Mourik, Pavel Hrmo, Ezra Kassa, Simon Ragg and Chiara De-caroli for fruitful discussion. This work was supported by the European Commission through project PIEDMONS 801285 and by the Institut für Quanteninformation GmbH. This work was supported by the European Commission also through the Marie Sklodowska-Curie Action, Grant Number: No 801110 (Erwin Schrödinger Quantum Fellowship Programme).


[37] The Panopticon setup owes its name to a type of institutional building proposed by the English philosopher and social theorist Jeremy Bentham [101]. In this kind of building, a single watchman located in a central tower can observe all the inmates of the institution, which are located in cells with optical clearance around the tower.


[52] Nanotech 250UPL, Moore Precision Tools.


[54] New developments in Atomic Layer Deposition (ALD) have shown promising results in uniform coating of com-plex 3D structures, making possible to reach reflectiv-ities close to 100% without damaging the mirror sur-face. See for example https://www.laseroptik.de/en/coating-guide/production-methods/ald.

Insulated Nichrome wires NC-32, LakeShore Cryotronics®.

NTC Thermistors BC101B1K, Littelfuse®.

KL-325K Silver Epoxy Glue.

Allectra 35S-TUBE-20 Ceramic tube, diameter 2 mm,.

Glass sphere diameter 2 mm.


X. Xie and S. Li, Handbook of Manufacturing Engineering and Technology, 1 (2013).


The wavefront distortions were measured using a high-resolution wavefront sensor, Phasics SID4-307, at Asphericon GmbH.

J. D. Siverns and Q. Quraishi, Quantum Information Processing 16, 314 (2017).

Information about this trap can be found in https://www.osti.gov/servlets/purl/1239095.


Al₂O₃ 96%, fabricated by ELCERAM a.s. Czech Republic.

Using the Gold conductor composition DuPont 5744R.

Knowles Syfer 0805Y1K00102KST, maximum voltage 1 kV.

Accu-Glass male gold pins type T-2, part number 110008.

The solder used is Solid Wire Solder, Lead Free, 430 F, item number SB61/2POP, 96% Tin, 4% Silver.

ISEG EHS 82 20p.

Rhode & Schwartz SMC100A, option B101).

MiniCircuits ZHL-1-2W+.


SmarAct SLC-1720-S-UHVT.

Kimball Physics, MCF800-SphSqa-G2E4C4A16.

VAT 54132-GE02.

Bayard-Alpert ion gauge, Agilent UHV-24.

SAES CapacitorTor Z400.

SAES NEXTorr D 100-5.

All the viewports are fabricated by VACOM GmbH and anti-reflection coated by Laseroptik GmbH.

VACOM VPCF63DUVQ-L-LAMBDAD10.

VACOM VPCF16GE-K.


Custom design fabricated by AlphaVaku® E.U., Austria.

Custom design fabricated by Testbourne Ltd, UK.